



40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D T _C = +25°C
40V	$4.7 \text{m}\Omega @ V_{GS} = 10V$	100A

Description and Applications

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

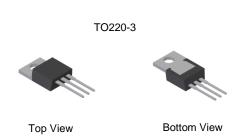
- **Engine Management Systems**
- **Body Control Electronics**
- **DC-DC Converters**

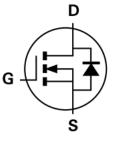
Features

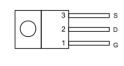
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low Input Capacitance
- Low Input/Output Leakage
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: TO220-3
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)







Equivalent Circuit

Top View Pin Out Configuration

Ordering Information (Note 4)

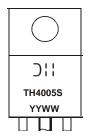
Part Number	Case	Packaging
DMTH4005SCT	TO220-3	50 Pieces/Tube

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and http://www.diodes.com/products/packages.html.

 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information



☐ ☐ Manufacturer's Marking TH4005S = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 16 = 2016) WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	40	V	
Gate-Source Voltage	V_{GSS}	±20	V	
Continuous Drain Current (Note 6)	T _C = +25°C		100	А
Continuous Drain Current (Note 6)	$T_{C} = +100^{\circ}C$	ID	78	
Maximum Continuous Body Diode Forward Current (Note 6)	T _C = +25°C	Is	100	Α
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	160	Α	
Avalanche Current, L=0.1mH	I _{AS}	32.5	Α	
Avalanche Energy, L=0.1mH	E _{AS}	52.8	mJ	

Thermal Characteristics

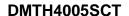
Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	P_{D}	2.8	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	52.8	°C/W
Total Power Dissipation (Note 6)	$T_C = +25^{\circ}C$	P_{D}	125	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	1.2	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

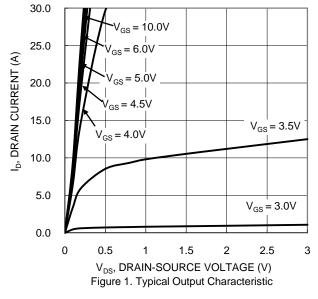
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	V	$V_{GS} = 0V$, $I_D = 1mA$	
Zero Gate Voltage Drain Current	I _{DSS}	I	_	1	μA	$V_{DS} = 32V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	I	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	$V_{GS(TH)}$	2	_	4	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	1	3.8	4.7	mΩ	$V_{GS} = 10V, I_D = 50A$	
Diode Forward Voltage	V_{SD}		_	1.2	V	$V_{GS} = 0V, I_{S} = 50A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss	1	3062	_		$V_{DS} = 20V$, $V_{GS} = 0V$, $f = 1MHz$	
Output Capacitance	Coss	l	902	_	pF		
Reverse Transfer Capacitance	Crss	1	179	_			
Gate Resistance	R_{G}		0.67	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Q_g	_	49.1	_		V _{DD} = 20V, I _D = 50A,	
Gate-Source Charge	Q_{gs}	_	10.3	_	nC		
Gate-Drain Charge	Q_{gd}	_	13	_		V _{GS} = 10V	
Turn-On Delay Time	t _{D(ON)}	I	8.7	_		$V_{DD} = 20V, V_{GS} = 10V,$ $I_{D} = 50A, R_{G} = 3\Omega$	
Turn-On Rise Time	t _R	_	6.8	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	I	18.6	_	115		
Turn-Off Fall Time	t _F	1	7.3	_			
Reverse Recovery Time	t _{RR}	-	31.8	_	ns	I= - 50 \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	
Reverse Recovery Charge	Q _{RR}	_	26.5		nC I _F = 50A, di/dt = 100A/μs		

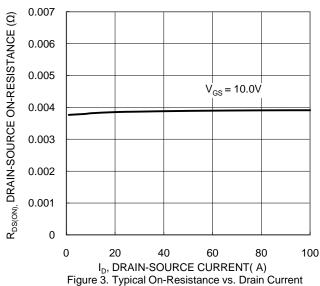
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on infinite heat sink. Notes:

- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.









and Gate Voltage

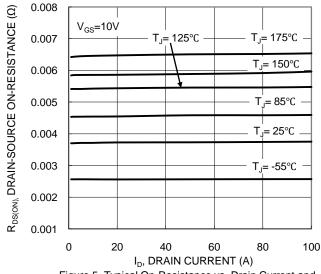
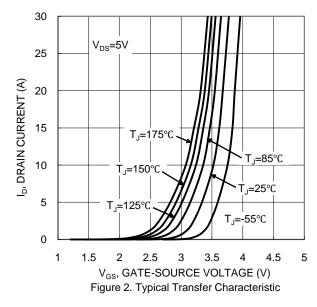
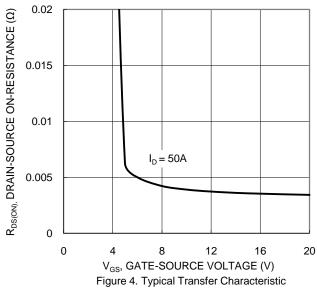


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





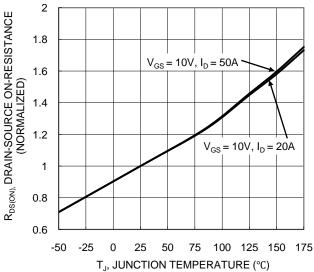
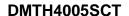


Figure 6. On-Resistance Variation with Temperature





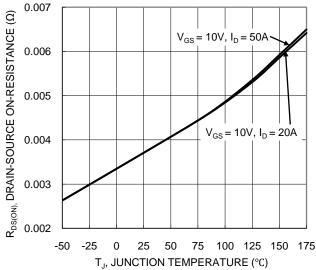
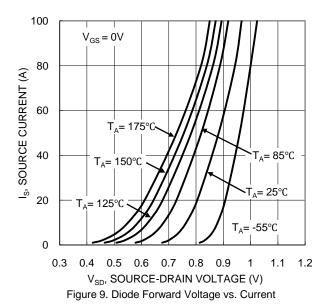
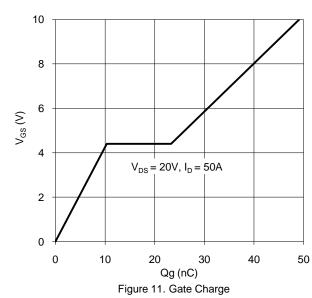


Figure 7. On-Resistance Variation with Temperature





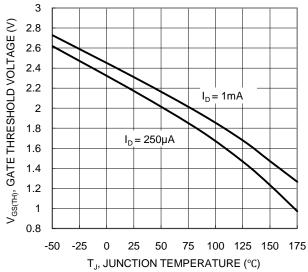
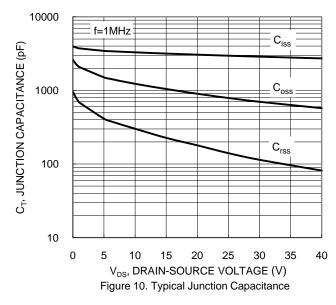
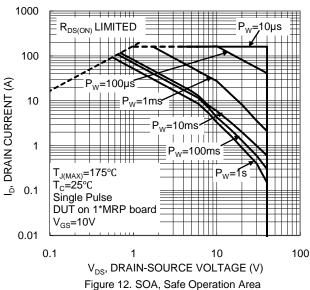


Figure 8. Gate Threshold Variation vs. Temperature







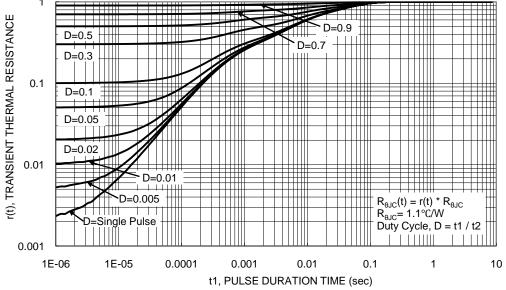
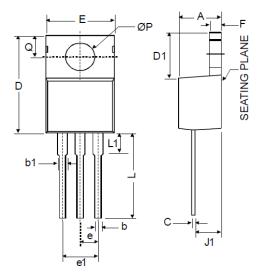


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



10220-3					
Dim	Min	Max			
Α	3.55	4.85			
b	0.51	1.14			
b1	1.14	1.78			
С	0.31	1.14			
D	14.20	16.50			
D1	5.84	6.86			
Е	9.70	10.70			
е	2.79	2.99			
e1	4.83	5.33			
F	0.51	1.40			
J1	2.03	2.92			
L	12.72	14.72			
L1	3.66	6.35			
Р	3.53	4.09			
Q	2.54	3.43			
All Dimensions in mm					



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